SWK4953

30V Dual P-Channel Enhancement-Mode MOSFET

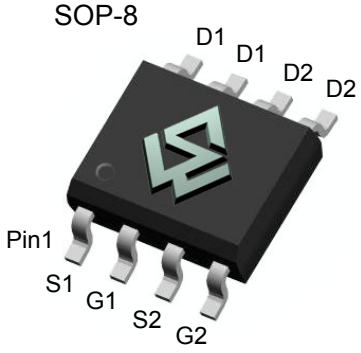
General Description

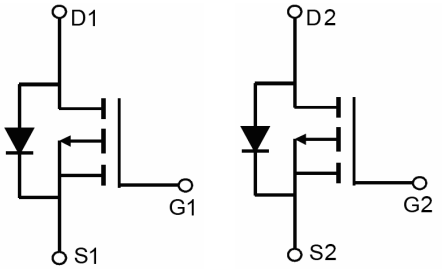
- Low gate charge.
- Use as a load switch.
- Use in PWM applications

Product Summary

- BV_{DSS} -30V
- $R_{DS(on)}$ @VGS = 10V < 60mΩ
- $R_{DS(on)}$ @VGS = 4.5V < 90mΩ

SOP-8





Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current (T_A=25ºC)	I_D	-5.3	A
Drain Current (T_A=75ºC)		-2.8	A
Pulsed Drain Current [a]	I_{DM}	-18	A
Power Dissipation [b] (T_A=25ºC)	P_D	2.5	W
Power Dissipation [b] (T_A=75ºC)		1.0	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	ºC

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Junction-to-Ambient [a] (t ≤ 10s)	$R_{\theta JA}$	50	ºC/W
Junction-to-Ambient [a,d] (Steady-State)		90	ºC/W
Junction-to-Lead (Steady-State)	$R_{\theta JL}$	25	ºC/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)						
Symbol	**Parameter**	**Conditions**	**Min**	**Typ**	**Max**	**Units**
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V , I_D = -250uA	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -24V , V_{GS} = 0V			-1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} , I_D = -250uA	-1		-2.5	V
$R_{DS(ON))}$	Drain-Source On-State Resistance	V_{GS} = -10V , I_D = -5.3A			60	mΩ
		V_{GS} = -4.5V , I_D = -4.5A			90	mΩ
g_{FS}	Forward Transconductance	V_{DS} = -10V , I_D = -5.3A		18		S
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS} = 0V , I_S = -1.0A			-1.3	V
I_S	Maximum Body-Diode Continuous Current				-2.0	A
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -15V , V_{GS} = 0V f = 1.0MHz		553		pF
C_{oss}	Output Capacitance			93		pF
C_{rss}	Reverse Transfer Capacitance			63		pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS} = -15V , I_D = -5.3A V_{GS} = -10V		12		nC
Q_{gs}	Gate-Source Charge			4		nC
Q_{gd}	Gate-Drain Charge			5		nC
$t_{D(ON)}$	Turn-On Delay Time	V_{DD} = -15V , ID = -1A V_{GS} = -10 V R_{GEN} = -6 ohm		14		ns
t_r	Turn-On Rise Time			5		ns
$t_{D(OFF)}$	Turn-Off Delay Time			20		ns
t_f	Turn-Off Fall Time			6		ns

a. Repetitive rating, Pulse width limited by junction temperature $T_{J(MAX)}$=150 ºC. Ratings are based on low frequency and duty cycles to keep initial T_J=25 ºC

b. The power dissipation P_D is based on $T_{J(MAX)}$=150 ºC , using≤10s junction-to-ambient thermal resistance.

c. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The value in any given application depends on the user's specific board design.

d. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.